



Expertise Applied | Answers Delivered

8755 W. Higgins Road  
Suite 500  
Chicago, IL 60631

[www.littelfuse.com](http://www.littelfuse.com)

## Product Change Notice (PCN)

Friday, September 19, 2025

### LFPCN250903WXC

#### Product Change Notification for Littelfuse 1200V & 1700V SiC MOSFET "LSIC1MO" series

##### Change categories

<input type="checkbox"/> Obsolescence/discontinuance	<input type="checkbox"/> Manufacturing site
<input type="checkbox"/> Technology	<input type="checkbox"/> Testing/qualification
<input checked="" type="checkbox"/> Material: second source of epi wafer	<input type="checkbox"/> Datasheet
<input type="checkbox"/> Process	<input type="checkbox"/> Other:

To our customers and partners,

Littelfuse would like to inform you about the qualification of two second sources of epi wafer material for its 1200V and 1700V Silicon Carbide MOSFET series "LSIC1MO".

These second sources will allow us to provide better service by reducing our production lead time and ensuring safety of supply for the MOSFETs.

The affected part numbers and a summary of the reliability test results are listed on page 2.

MOSFET built using either source of epi wafers are equivalent in function, performance and quality.

There is no change in datasheet parameters.

Qualification reports are available on request; a summary is provided on page 3.

Lack of acknowledgement of this PCN until December 16<sup>th</sup>, 2025 constitutes an acceptance of the PCN.

Please contact your Regional Sales representative or Field Application Engineer for any inquiry.

Best Regards,  
Francois Perraud  
Sr. Manager, product management  
Littelfuse, Inc.

[FPerraud@Littelfuse.com](mailto:FPerraud@Littelfuse.com)



Expertise Applied | Answers Delivered

8755 W. Higgins Road  
Suite 500  
Chicago, IL 60631

[www.littelfuse.com](http://www.littelfuse.com)

## Product Change Notice (PCN)

### Affected part numbers

Part number	Description
LSIC1MO120E0080	1200V, 80mΩ SiC MOSFET in TO247-3L
LSIC1MO120E0120	1200V, 120mΩ SiC MOSFET in TO247-3L
LSIC1MO120E0160	1200V, 160mΩ SiC MOSFET in TO247-3L
MCL10P1200LB	1200V, 160mΩ SiC MOSFET half bridge in SMPD
LSIC1MO170E0750	1700V, 750mΩ SiC MOSFET in TO247-3L
LSIC1MO170H0750	1700V, 750mΩ SiC MOSFET in TO268-HV
LSIC1MO170T0750	1700V, 750mΩ SiC MOSFET in TO263-HV

### Summary of changes

#### Changes in form

The new epi wafers use a different passivation material as compared with the already qualified wafers.

#### Changes in function

There are no changes in function or performance.



Expertise Applied | Answers Delivered

8755 W. Higgins Road  
Suite 500  
Chicago, IL 60631

[www.littelfuse.com](http://www.littelfuse.com)

## Product Change Notice (PCN)

### Reliability test summary

MOSFET Wafer Supplier Qualification					
TEST	CONDITION	ENDPOINT	DEVICE	New epi supplier	RESULT
HTRB	JESD22-A108, 175° C	1008 hours	LSIC1MO120E0080	A	0/20
			LSIC1MO120E0160	B	0/20
			LSIC1MO170T0750	B	0/80
HTGB pos	JESD22-A108, 175° C	1008 hours	LSIC1MO120E0080	A	0/20
			LSIC1MO120E0160	B	0/20
			LSIC1MO170E0750	B	0/20
HTGB neg	JESD22-A108, 175° C	1008 hours	LSIC1MO120E0080	A	0/20
			LSIC1MO120E0160	B	0/20
			LSIC1MO170E0750	B	0/20
Temperature Cycle	JESD22-A104 (-55°C to 150°C)	1000 cycles	LSIC1MO120E0080	A	0/20
			LSIC1MO120E0160	B	0/80
			LSIC1MO170T0750	B	0/20
H3TRB	JESD22-A110 (130° C, 85% RH)	1008 hours	LSIC1MO120E0080	A	0/20
			LSIC1MO120E0160	B	0/20
			LSIC1MO170E0750	B	0/20
HV H3TRB	JESD22-A110 (130° C, 85% RH)	1008 hours	LSIC1MO120E0080	A	0/20
IOL	JESD22-A105	3000 cycles	LSIC1MO120E0080	A	0/20
			LSIC1MO120E0160	B	0/20
			LSIC1MO170E0750	B	0/20